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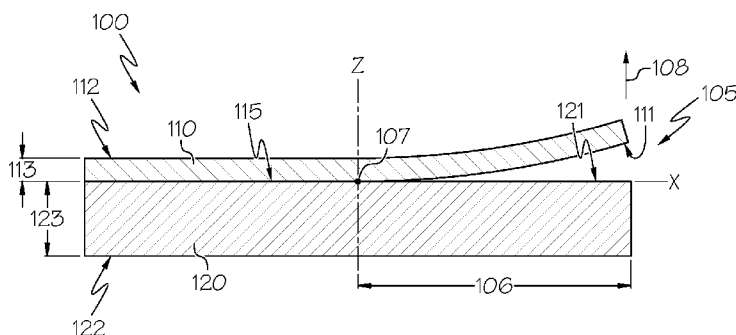


FIG. 1

(57) Abstract: Methods of processing a first substrate bonded to a second substrate include moving a wire along an interface to propagate a debonding front and debond the first substrate from the second substrate. In some embodiments, the first substrate includes a thickness less than or equal to about 300 μm . In further embodiments, the wire includes a tensile strength less than a critical failure stress of the first substrate. In still further embodiments, the wire is configured to conform to a shape of the debonding front during the step of moving the wire such that one or more edges of the first substrate are debonded from the second substrate prior to a debonding of a corresponding interior portion of the first substrate from the second substrate.

METHODS FOR PROCESSING A FIRST SUBSTRATE BONDED TO A SECOND SUBSTRATE

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application claims the benefit of priority under 35 U.S.C. § 119 of U.S. Provisional Application Serial No. 62/248823 filed on October 30, 2015, the content of which is relied upon and incorporated herein by reference in its entirety.

FIELD

[0002] The present disclosure relates generally to methods for processing a first substrate bonded to a second substrate and, more particularly, to methods for debonding a first substrate from a second substrate.

BACKGROUND

[0003] Glass substrates are commonly used, for example, in display applications, including liquid crystal displays (LCDs), electrophoretic displays (EPD), organic light emitting diode displays (OLEDs), plasma display panels (PDPs), or the like. Such glass substrates are commonly fabricated from a glass ribbon drawn from a quantity of molten material using a wide variety of glass ribbon forming techniques (e.g., slot draw, float, down-draw, fusion down-draw, and up-draw). The glass substrate may be bonded to a second substrate (e.g., a carrier substrate) to facilitate handling of the glass substrate when processing the glass substrate. Once processing of the glass substrate is complete, the glass substrate can be debonded from the second substrate. However, some conventional debonding techniques can be difficult, time consuming and may even result in damage to the glass substrate. Indeed, typical debonding techniques may result in failure of the glass substrate (e.g., breaking of the glass substrate), cracking of the glass substrate, and/or introduction of edge imperfections that reduce the strength of the glass substrate.

SUMMARY

[0004] There are set forth methods and apparatus for debonding a first substrate from a second substrate. In some examples, the present disclosure provides debonding of the first substrate from the second substrate with a thin pliable wire that reduces flexing of the first substrate during debonding. As the bending of the first substrate is reduced during debonding, relatively less bending stress is introduced to the first substrate during the debonding process. Furthermore, the flexibility of the wire can allow the wire to conform to the debonding front, thus relieving stress that might otherwise develop due to interaction with

sharp transitions that may occur because of glass flaws. Consequently, the debonding techniques of the present disclosure provides a technical benefit of debonding the first substrate from the second substrate with reduced chance of damaging the glass substrate (e.g., by cracking, breaking, etc.) when compared to other conventional debonding techniques. As used herein a “glass substrate” may comprise glass, glass-ceramic, ceramic, or silicon wafer.

[0005] In a first embodiment, a method of processing a first substrate bonded to a second substrate includes initiating an opening at an interface between the first substrate and the second substrate, inserting a wire into the opening, and moving the wire along the interface to propagate a debonding front and debond the first substrate from the second substrate. In one example of the first embodiment, the first substrate includes a thickness less than or equal to about 300 μm . In another example of the first embodiment, the wire includes a diameter from about 50 μm to about 300 μm . In still another example of the first embodiment, the wire includes a tensile strength from about 25 MPa to about 10 GPa. In yet another example of the first embodiment, the wire is pliable. For instance, the pliable wire can include at least one of polytetrafluoroethylene (PTFE), nylon, and fluorocarbon. In a further example of the first embodiment, the method further includes maintaining at least a minimum separation distance between a debonded portion of the first substrate and a corresponding portion of the second substrate. In one example, the minimum separation distance is greater than or equal to a diameter of the wire. In another example, the minimum separation distance is maintained over an entire debonded length of the first substrate. In still a further example of the first embodiment, the wire includes a first tensile strength less than a critical failure stress of the first substrate. In one example, the method further comprises the steps of removing the wire and inserting a new wire between the first substrate and the second substrate. In such an example, the method further includes the step of moving the new wire along the interface to further propagate the debonding front and further debond the first substrate from the second substrate, wherein the new wire includes a second tensile strength greater than the first tensile strength and less than the critical failure stress of the first substrate. The first embodiment may be provided alone or in combination with any one or more of the examples of the first embodiment discussed above.

[0006] In a second embodiment, a method of processing a first substrate bonded to a second substrate includes moving a wire along an interface between the first substrate and the second substrate to propagate a debonding front and debond the first substrate from the second substrate. The first substrate includes a thickness less than or equal to about 300 μm , and wherein the wire includes a tensile strength less than a critical failure stress of the first

substrate. In one example of the second embodiment, the method further includes maintaining a debond angle substantially constant during the step of moving the wire. In another example of the second embodiment, prior to the step of moving the wire, the method includes increasing a bond strength between the first substrate and the second substrate by raising the temperature of the first substrate and the second substrate to a temperature of at least about 150°C. In still another example of the second embodiment, prior to the step of moving the wire, the method includes applying functional components to a major surface of the first substrate facing away from the second substrate bonded to the first substrate. In yet another example of the second embodiment, the step of moving the wire entirely debonds the first substrate from the second substrate. The second embodiment may be provided alone or in combination with any one or more of the examples of the second embodiment discussed above.

[0007] In a third embodiment, a method of processing a first substrate bonded to a second substrate includes initiating an opening at an interface between the first substrate and the second substrate. The method further includes the steps of inserting a wire into the opening and moving the wire along the interface to propagate a debonding front and debond the first substrate from the second substrate. The wire is configured to conform to a shape of the debonding front during the step of moving the wire such that one or more edges of the first substrate are debonded from the second substrate prior to a debonding of a corresponding interior portion of the first substrate from the second substrate. In one example of the third embodiment, the shape of the debonding front is concave with respect to a direction of propagation of the debonding front. In another example of the third embodiment, the wire is configured to at least one of yield and fail prior to a failure of the first substrate. In still another example of the third embodiment, a bond strength at the debonding front is defined based, at least in part, on at least one of a wafer bonding between the first substrate and the second substrate and a bonding agent between the first substrate and the second substrate. The third embodiment may be provided alone or in combination with any one or more of the examples of the third embodiment discussed above.

[0008] Further embodiments may be provided by any combination of the first embodiment, second embodiment and/or third embodiment either alone or in combination with any one or more of the examples of the corresponding embodiments in the combination.

BRIEF DESCRIPTION OF THE DRAWINGS

[0009] The above and other features, aspects and advantages are better understood when the following detailed description of the disclosure is read with reference to the accompanying drawings, in which:

[0010] **FIG. 1** shows an example initial step of debonding a first substrate from a second substrate by initiating an opening at an interface between the first substrate and the second substrate;

[0011] **FIG. 2** shows a schematic illustration of a cantilever beam;

[0012] **FIG. 3** is a sectional view of the cantilever beam along line 3-3 of **FIG. 2**;

[0013] **FIG. 4** shows an example schematic cross sectional view of a first substrate being debonded from a second substrate with a wire in accordance with aspects of the disclosure;

[0014] **FIG. 5** shows another example schematic cross sectional view of a first substrate being debonded from a second substrate with a wire in accordance with aspects of the disclosure;

[0015] **FIG. 6** shows yet another example schematic cross sectional view of a first substrate being debonded from a second substrate with a wire in accordance with aspects of the disclosure; and

[0016] **FIG. 7** shows a schematic view of a first substrate being debonded from a second substrate with a wire in accordance with aspects of the disclosure.

DETAILED DESCRIPTION

[0017] Exemplary embodiments will now be described more fully hereinafter with reference to the accompanying drawings. Whenever possible, the same reference numerals are used throughout the drawings to refer to the same or like parts. However, subject matter encompassed by the claims may be embodied in many different forms and should not be construed as limited to the embodiments set forth herein.

[0018] Directional terms as used herein (e.g., up, down, right left, front, back, top, bottom) are made only with reference to the figures as drawn and are not intended to imply absolute orientation.

[0019] Embodiments can be used to facilitate removal of a first substrate bonded to a second substrate. For instance, some embodiments can facilitate initial, partial or even complete separation of a first substrate (e.g., a glass substrate) from a second substrate (e.g., a carrier substrate).

[0020] In just some embodiments, the first substrate of the disclosure can comprise a flexible glass substrate although the first substrate of the present disclosure can comprise

other types of substrates. Flexible glass substrates are often used to manufacture liquid crystal displays (LCDs), electrophoretic displays (EPD), organic light emitting diode displays (OLEDs), plasma display panels (PDPs), touch sensors, photovoltaics, etc. To enable the handling of flexible glass substrates during processing, a flexible glass substrate may be bonded to a relatively rigid second substrate, for example with a bonding agent (e.g., a polymer bonding agent, or bonding agents as discussed in WO2014/093775, WO2014/093193, WO2015/113020, WO2015/113023, WO2015/112958, WO2015/157202, US62/185,095, or US62/201,245).

[0021] In some embodiments, the second substrate and the first substrate bonded to the second substrate can each include a thickness defined between the respective major surfaces of the substrates. The second substrate can optionally introduce a desired level of rigidity by providing the second substrate with a thickness that is greater than the thickness of the first substrate that is removably bonded to the second substrate. In addition or alternatively, in some embodiments, the second substrate can be selected with a thickness wherein the overall thickness of the second substrate and the first substrate bonded to the second substrate is within a range that can be used with existing processing machinery configured to process relatively thick glass substrates having a thickness within the range of the overall thickness of the second substrate and the first substrate bonded to the second substrate. In such instances, the second substrate may be thinner than the first substrate, yet still provide the desired thickness and/or rigidity to the combined article for processing.

[0022] The rigid characteristics and size of the second substrate allow the bonded first substrate to be handled in production without significant bending that may otherwise cause damage to the first substrate (e.g., flexible glass substrate and/or functional components mounted to the flexible glass substrate). After processing (e.g., handling, adding components, treating, etc.), some embodiments may be used to initially or completely remove the second substrate from the first substrate (e.g., glass substrate or silicon wafer), or to remove the first substrate(s) from the second substrate.

[0023] As shown in **FIG. 1**, a composite substrate **100** can include a first substrate **110**, for example a glass substrate (e.g., a thin, flexible glass substrate), a silicon wafer or other relatively thin substrate. The first substrate **110** may be formed of any suitable material including glass, glass-ceramic or ceramic, as examples, and may or may not be transparent. When made of glass, the first substrate **110** may be of any suitable composition, including alumino-silicate, boro-silicate, alumino-boro-silicate, soda-lime-

silicate, and may be either alkali containing or alkali free depending upon its ultimate application.

[0024] The first substrate **110** includes a first major surface **111** parallel to a second major surface **112**. The first major surface **111** of the first substrate **110** may be bonded to a first major surface **121** of a second substrate **120**. Moreover, the second major surface **112** of the first substrate **110** may optionally be thin film coated depending on at least one of an intended application and process condition.

[0025] The first major surface **111** and the second major surface **112** of the first substrate **110** are separated from each other by an average thickness **113**. In one embodiment, the average thickness **113** of the first substrate **110** can be less than or equal to about 300 μm (e.g., “ultra-thin”), for example from about 40 μm to about 300 μm , for example from about 40 μm to about 280 μm , for example from about 40 μm to about 260 μm , for example from about 40 μm to about 240 μm , for example from about 40 μm to about 220 μm , for example from about 40 μm to about 200 μm , for example from about 40 μm to about 180 μm , for example from about 40 μm to about 160 μm , for example from about 40 μm to about 140 μm , for example from about 40 μm to about 120 μm , for example from about 40 μm to about 100 μm , for example from about 40 μm to about 80 μm , for example from about 40 μm to about 60 μm , for example from about 60 μm to about 300 μm , for example from about 80 μm to about 300 μm , for example from about 90 μm to about 300 μm , for example from about 100 μm to about 300 μm , for example from about 110 μm to about 300 μm , for example from about 120 μm to about 300 μm , for example from about 130 μm to about 300 μm , for example from about 140 μm to about 300 μm , for example from about 150 μm to about 300 μm , for example from about 160 μm to about 300 μm , for example from about 170 μm to about 300 μm , for example from about 180 μm to about 300 μm , for example from about 190 μm to about 300 μm , for example from about 200 μm to about 300 μm , for example from about 210 μm to about 300 μm , for example from about 220 μm to about 300 μm , for example from about 230 μm to about 300 μm , for example from about 240 μm to about 300 μm , for example from about 250 μm to about 300 μm , for example from about 260 μm to about 300 μm , for example from about 270 μm to about 300 μm , for example from about 280 μm to about 300 μm , for example from about 290 μm to about 300 μm , for example from about 50 μm to about 300 μm , for example from about 60 μm to about 290 μm , for example from about 70 μm to about 280 μm , for example from about 80 μm to about 270 μm , for example from about 90 μm to about 260 μm , for example from about 100 μm to about 250 μm , for example from about 110 μm to about 240 μm , for

example from about 120 μm to about 230 μm , for example from about 130 μm to about 220 μm , for example from about 140 μm to about 210 μm , for example from about 150 μm to about 200 μm , for example from about 160 μm to about 190 μm , for example from about 170 μm to about 180 μm , and all subranges of average thicknesses therebetween.

[0026] As further shown in **FIG. 1**, the composite substrate **100** may include the second substrate **120**, for example a glass substrate, that may be of any suitable material including glass, glass-ceramic, ceramic and composites of organic and inorganic materials, and may or may not be transparent. If made of glass, the second substrate **120** may be of any suitable composition including alumino-silicate, boro-silicate, alumino-boro-silicate, soda-lime-silicate, and may be either alkali containing or alkali-free depending upon its ultimate application. In some embodiments, the second substrate may be formed from a material (e.g., the materials mentioned above) capable of withstanding a high temperature processing technique where the temperature of the first substrate and the second substrate may reach a temperature of at least about 150°C, for example from about 150°C to about 900°C, for example from about 150°C to about 700°C, for example from about 150°C to about 600°C, and all subranges therebetween. The second substrate **120** may be made of one layer or multiple layers (including multiple thin sheets) that are bonded together to form a part of the composite substrate **100**. The second substrate **120** may be a same or similar size and/or shape or of a different size and/or shape as the first substrate **110**.

[0027] The second substrate **120** includes a second major surface **122** parallel to the first major surface **121**. The first major surface **121** and the second major surface **122** of the second substrate **120** are separated from each other by an average thickness **123**. In some embodiments, the average thickness **123** can be greater than the thickness of the first substrate **110**. Providing a relatively thicker second substrate can help increase the effective stiffness and thickness of the composite substrate **100** to allow the first substrate to be processed with machinery designed to process substrates having a relatively greater thickness and/or a relatively greater stiffness than those possessed by the first substrate **110**. In some embodiments, the second substrate **120** has a higher rigidity than the first substrate **110**.

[0028] In some embodiments, the average thickness **123** of the second substrate **120** can be from about 200 μm to about 700 μm , for example from about 250 μm to about 700 μm , for example from about 300 μm to about 700 μm , for example from about 350 μm to about 700 μm , for example from about 400 μm to about 700 μm , for example from about 450 μm to about 700 μm , for example from about 500 μm to about 700 μm , for example from about 550 μm to about 700 μm , for example from about 600 μm to about 700 μm , for

example from about 650 μm to about 700 μm , and all subranges of average thicknesses therebetween.

[0029] In further embodiments, the average thickness **123** of the second substrate **120** can be from about 200 μm to about 650 μm , for example from about 200 μm to about 600 μm , for example from about 200 μm to about 550 μm , for example from about 200 μm to about 500 μm , for example from about 200 μm to about 450 μm , for example from about 200 μm to about 400 μm , for example from about 200 μm to about 350 μm , for example from about 2000 μm to about 3000 μm , for example from about 200 μm to about 250 μm , and all subranges of average thicknesses therebetween.

[0030] In still further embodiments, the average thickness **123** of the second substrate **120** can be from about 250 μm to about 600 μm , for example from about 300 μm to about 550 μm , for example from about 350 μm to about 500 μm , for example from about 400 μm to about 450 μm , and all subranges of average thicknesses therebetween.

[0031] The composite substrate **100** can be designed to operate with devices and apparatus based on existing or future infrastructure utilized with respect to manufacturing processes. The first substrate **110** may be bonded to the second substrate **120** at an interface **115**. For example, the first major surface **111** of the first substrate **110** can be bonded to the first major surface **121** of the second substrate **120** at the interface **115**. The bond between the first substrate **110** and the second substrate **120** can be based at least in part on at least one of wafer bonding, a bonding agent (e.g., a benign bonding agent that temporarily bonds the substrates together for processing yet allows them to be released from one another after processing), and a thermal annealing cycle. The bond between the first substrate **110** and the second substrate **120** can therefore be based at least in part on a chemical bond at the interface **115**.

[0032] To achieve a desired bond strength between the first substrate **110** and the second substrate **120**, a bonding material may be heated, cooled, dried, mixed with other materials, or reaction induced, and pressure may be applied to the first substrate **110** and the second substrate **120**. As used herein, “bond strength” refers to any one or more of dynamic shear strength, dynamic peel strength, static shear strength, static peel strength and combinations thereof. Peel strength, for example, is the force per unit width necessary to initiate failure (e.g., static) and/or to maintain a specified rate of failure (e.g., dynamic) by means of a stress applied to one or both of the first substrate **110** and second substrate **120** in a peeling mode. Shear strength is the force per unit width necessary to initiate failure (e.g., static) and/or maintain a specified rate of failure (e.g., dynamic) by means of a stress

applied to one or both of the first substrate **110** and second substrate **120** in a shear mode. Any suitable methods can be used to determine bond strength including any suitable peel and/or shear strength tests. For example, the energy of adhesion (i.e., bond energy or bond strength) between two surfaces can be measured by a double cantilever beam method or wedge test. The tests simulate in a qualitative manner the forces and effects on an adhesive bond joint at a modification layer / first sheet interface. Wedge tests are commonly used for measuring bonding energy. For example, ASTM D5041, Standard Test Method for Fracture Strength in Cleavage of Adhesives in Bonded Joints, and ASTM D3762, Standard Test Method for Adhesive-Bonded Surface Durability of Aluminum, are standard test methods for measuring bonding of substrates with a wedge. Also, for example, one method of measuring bond strength is set forth in US62/201,245, filed on August 5, 2015.

[0033] The first substrate **110**, in the form of a glass substrate, can be used in a variety of applications including but not limited to display and touch applications. In addition, the first substrate **110** can be flexible and conformable and can withstand high temperatures, along with the second substrate **120**. For example, the first substrate and the second substrate can be heated at a temperature of at least about 150°C during processing of the first substrate **110**, for example a temperature from about 150°C to about 900°C, for example from about 150°C to about 700°C, for example from about 150°C to about 600°C, and all subranges therebetween. In some embodiments where the first substrate **110** comprises a glass substrate and the glass substrate, along with the second substrate, are heated at a temperature of at least about 150°C during a processing technique for example adding functional components to the glass substrate. In further embodiments, the temperature of at least about 150°C is from about 150°C to about 700°C, for example from about 400°C to about 700°C, for example from about 550°C to about 650°C, and all subranges therebetween. To provide a manner in which to handle and support the first substrate **110**, the first substrate **110** can be bonded to the second substrate **120** which may be thicker and/or provide a higher rigidity to the first substrate **110** than the first substrate **110** possesses alone. Once processing is complete, the first substrate **110** can be debonded from the second substrate **120**.

[0034] Exemplary methods of debonding the first substrate **110** from the second substrate **120** include initiating an opening **105** at the interface **115** between the first substrate **110** and the second substrate **120**. The opening **105** can be initiated by applying a force **108** (e.g., a debond force) in a direction opposing the bond between the first substrate **110** and the second substrate **120** at the interface **115**. In addition or alternatively, a razor blade or at least

one of a sharp, thin, and flat object can be used to initiate the opening **105** by inserting an edge of the razor blade or the at least one of a sharp, thin, and flat object at the interface **115** between the first major surface **111** of the first substrate **110** and the first major surface **121** of the second substrate **120**. When the opening **105** is initiated, a debonding front **107** is formed. In some embodiments, an effective crack tip length **106** may develop that, for purposes of the disclosure, is defined as the distance between the debonding front **107** and the force **108** as shown in **FIGS. 1 and 4-7**.

[0035] Throughout the disclosure, the debonding front **107** means a periphery of the interface **115** where, on one side of the periphery of interface **115**, the first substrate **110** and the second substrate **120** are bonded together; and, on another side of the periphery of the interface **115**, the first substrate **110** and the second substrate **120** are debonded from one another. As shown in the top view of **FIG. 7**, the debonding front **107** extends with a curved profile, for example the illustrated curved shape that can be curvilinear (e.g., concave) in the direction of propagation **130** of the debonding front **107**. As discussed below, the curvilinear shape of the debonding front **107** can reduce stress on the edges of the first substrate (e.g., glass substrate), thereby reducing the likelihood of failure of the first substrate due to imperfections at the edges that may result in the edges being relatively fragile when compared to the corresponding interior portion of the first substrate. Although the debonding front **107** is illustrated with a concave shape, other curvilinear shapes may be provided. In addition or in the alternative, the debonding front **107** can be at least partially or entirely straight, rectilinear (e.g., stepped) or another suitable shape.

[0036] It is to be understood that and with continued reference to **FIGS. 1 and 4-7**, in some embodiments, the interface **115** between the first substrate **110** and the second substrate **120** may be less than a few nanometers in scale such that the physical behavior and characteristics of the first substrate **110** and the second substrate **120** at or near the debonding front **107** are based at least in part on a theoretical or hypothetical understanding of the nature of bonding between the first substrate **110** and the second substrate **120**. Such theoretical or hypothetical understanding of the nature of bonding between the first substrate **110** and the second substrate **120** may or may not be identical to actual physical behavior and characteristics of the first substrate **110** and the second substrate **120** at or near the debonding front **107**. Moreover, due to the relatively small thickness of the interface **115**, debonding characteristics that can be perceived by, for example, a human eye, at the debonding front **107** may differ from that which actually occurs at the debonding front **107** when debonding of the first substrate **110** from the second substrate **120**.

[0037] Turning to FIG. 2, a schematic 200 of a cantilevered beam 210 subjected to an applied end load **P** is provided to illustrate an approximation of stress produced in the first substrate 110 at the debonding front 107 (e.g., corresponding approximately to location 207 of the cantilevered beam 210) during a debonding process. The first substrate 110 can be pristine and defect free. In some embodiments, however, due to the thin nature of the first substrate 110, the first substrate 110 may be susceptible to high bending stresses. High bending stresses may arise during one or more processes to which the composite substrate 100 may be subjected, including the process of debonding the first substrate 110 from the second substrate 120. For example, the stress (σ) produced in the cantilevered beam 210 at location 207 can be approximated using the following equations, where **P** represents the applied end load, **L** represents the span of the cantilevered beam 210, **b** represents the width of the cantilevered beam 210 (see FIG. 3), and **h** represents the height of the cantilevered beam 210 (see FIG. 3):

$$[0038] \quad \sigma = \frac{PL}{Z} \quad (1)$$

$$[0039] \quad \Delta = \frac{PL^3}{3EI} \quad (2)$$

$$[0040] \quad I = \frac{bh^3}{12} \quad (3)$$

$$[0041] \quad Z = \frac{bh^2}{6} \quad (4)$$

$$[0042] \quad \sigma = \frac{6P}{b} \times \frac{L}{h^2} \quad (5)$$

[0043] The above approximation of the stress (σ) at location 207 of the cantilevered beam 210 indicates that the bending stress (σ) at location 207 increases when the span **L** increases and increases at a higher rate when the height **h** decreases. Moreover, as the span **L** increases, an initial mode (e.g., mode I) of debonding or delamination (e.g., pure lift off of the first substrate 110 from the second substrate 120) shifts to both mode I and shear (e.g., mode II). Thus, to propagate the debonding front 107, the applied load **P** can be increased. In addition, because the stress at the debonding front 107 will counter the direction of the applied load **P**, it is possible that propagation of the debonding front 107 may be arrested. Such a scenario leads to a monotonic increase of the bending stress (σ) in the first substrate

110 and an increase in tensile stress at the debonding front **107**. The bending stress (σ) can interact with flaws or other imperfections present in the first substrate **110** (e.g., along edges of the first substrate **110**) and can cause failure of the first substrate **110** (e.g., cracking, breaking, fracture, or catastrophic failure). Accordingly, the methods and apparatus of the present disclosure can debond the first substrate **110** from the second substrate **120** while keeping the bending stress (σ) below a level (e.g., critical level or critical limit) that would otherwise cause failure of the first substrate **110**. The critical level can be based at least in part on at least one of flaws or imperfections present in the first substrate **110**, the thickness of the first substrate **110** (e.g., defined by average thickness **113**), a quality of the first substrate **110** including a quality of edges of the first substrate **110** and a quality of cutting of edges of the first substrate **110**.

[0044] As shown in **FIG. 4**, a method and apparatus of debonding the first substrate **110** from the second substrate **120** can include inserting a wire **125** into the opening **105**. The method further includes moving the wire **125** along the interface **115** (e.g., along a direction of propagation **130** of the debonding front **107**) to propagate the debonding front **107** and debond the first substrate **110** from the second substrate **120** as shown in **FIGS. 5** and **6**. It is to be understood that any movement of the wire **125** is contemplated herein and is considered to be within the scope of disclosure, including but not limited to movement (e.g., at least one of translation and rotation) along any one or more directions (e.g., **X**, **Y**, **Z**) either alone or in combination. Moreover, the wire **125** may be pulled manually (e.g., by hand) or automatically (e.g., by machine, device, or apparatus) in any one or more longitudinal, lateral, or planar direction along the interface **115** between the first substrate **110** and the second substrate **120**. The wire **125** (e.g., movement of the wire) breaks the bond at the interface **115** between the first substrate **110** and the second substrate by imparting a force **108** that separates the first substrate **110** from the second substrate **120**. In other embodiments, external assistance (e.g., UV radiation, thermal energy, sonic energy, air pressure) may also be used to reduce or weaken the bond strength at the interface **115** between the first substrate **110** and the second substrate **120**.

[0045] In some embodiments, the wire **125** can include a diameter from about 50 μm to 300 μm , for example from about 50 μm to about 250 μm , for example from about 50 μm to about 200 μm , for example from about 50 μm to about 150 μm , for example from about 50 μm to about 100 μm , for example from about 100 μm to about 300 μm , for example from about 150 μm to about 300 μm , for example from about 200 μm to about 300 μm , for example from about 250 μm to about 300 μm , for example from about 75 μm to about 300

μm, for example from about 100 μm to about 250 μm, for example from about 150 μm to about 200 μm, and all subranges of average thicknesses therebetween.

[0046] In another embodiment, the wire **125** can be a pliable wire including resilient polymers. In some examples, the pliable wire can include resilient polymers selected from at least one of polytetrafluoroethylene (PTFE), nylon, and fluorocarbon. In other examples, the wire may include other materials, for example, metal, cotton, wool, glass, or rubber. The term wire, as used herein, is meant to encompass other similar structures, for example, cable, chain, cord, fiber, filament, rod, rope, strand, thread, yarn, multi- or mono element members as well as braided or otherwise stranded members made of the foregoing. In some examples, the wire (or components thereof) may have a core and cladding type of structure wherein each of these parts is made of the same or of a different material.

[0047] In some embodiments, the wire **125** can include a tensile strength within a range of about 25 MPa to 10 GPa. In addition or alternatively, the wire **125** can optionally include a tensile strength less than a critical failure stress of the first substrate **110**. For purposes of this disclosure, the critical failure stress of the first substrate can be determined by the four point bend test. During the four point bend test, the first substrate is loaded along two parallel top inner rollers while the first substrate is being supported along two parallel outer rollers. The critical failure stress is the stress that the first substrate fails under the four point bend test. In some embodiments, the critical failure stress of the first substrate **110** (e.g., glass substrate) can be greater than 25 MPa and even greater than 10 GPa.

[0048] Providing the wire **125** with a tensile strength that is less than the critical failure stress of the first substrate **110** allows the wire fail prior to inducing failure of the first substrate, thereby protecting the first substrate from being critically damaged by stresses produced by the wire. Furthermore, the wire used during debonding is relatively inexpensive to replace. Thus, even if the wire **125** fails (e.g., at least one of yields and fails), the method can further include inserting a new wire between the first substrate **110** and the second substrate **120**, and moving the new wire along the interface **115** to further propagate the debonding front **107** to continue debonding the first substrate **110** from the second substrate **120**. In some embodiments, the new wire can include a second tensile strength greater than the first tensile strength and less than the critical failure stress of the first substrate **110**. Thus, the new wire will be less likely to fail than the original wire while still protecting the first substrate from being critically damaged by stresses produced by the new wire.

[0049] The effective crack tip length **106** can be relatively small due to the relatively small diameter of the wire **125**. As such, bending stress at the debonding front **107** remains

relatively low even under the force **108** that breaks the bonds between the first substrate **110** and the second substrate **120**. During the step of moving the wire **125**, a debond angle **109**, defined as an angle between a debonded portion of the first substrate **110** and a corresponding portion of the second substrate **120** measured at an effective crack tip length **106** behind the debonding front **107**, can remain about constant. Thus, the bending stress at the debonding front **107** can remain substantially constant during the debonding process. Turning to **FIGS. 5 and 6**, the wire **125** can be moved to propagate the debonding front **107** and debond the first substrate **110** from the second substrate **120**. A debonded portion of the first substrate **110** includes a debonded length **104** that extends behind the wire **125**. As shown in **FIG. 5**, in one embodiment, the debonded length **104** can comprise a sag length wherein a portion of the debonded length of the first substrate **110** may sag and come into contact with the second substrate **120**. Subsequent contact between the portion of the debonded length of the first substrate **110** and the second substrate **120** can undesirably result in rebonding between the first substrate and the second substrate. Alternatively, the debonded length **104** can have an overhang length (i.e., a length that does not result in contact between the first substrate and the second substrate). Preventing contact between the first substrate and the second substrate with the overhang length can prevent undesirable rebonding between the first substrate and the second substrate. However, an overhang length that is not supported, as well as a sag length, can result in unwanted pressure to the wire **125** due to the weight of the debonded length being imposed and even leveraged onto the wire **125**. Consequently, the unwanted pressure on the wire **125** can increase the tensile stress on the wire **125** as it is being used to debond the first substrate from the second substrate. The unwanted increase in tensile stress on the wire **125** may result in unfortunate failure of the wire **125** during the debonding process.

[0050] To reduce pressure on the wire, **FIG. 6** illustrates an embodiment where the method can optionally include the step of providing the debonded length **104** as an overhang length while supporting the overhang length to maintain a minimum separation distance **103** between a debonded portion of the first substrate **110** and a corresponding portion of the second substrate **120**. Supporting the overhang length can reduce, for example eliminate, additional pressure on the wire **125**. Consequently, as pressure on the wire is reduced, the additional tensile stress that would have been imposed on the wire due to the unsupported overhang length can be reduced or eliminated. In some embodiments, the minimum separation distance **103** is greater than or equal to a diameter of the wire **125** to reduce, for example eliminate, pressure on the wire that may result from leveraged pinching of the wire

between the first substrate and the second substrate. To even further reduce, for example eliminate, pressure on the wire, the minimum separation distance **103** is maintained over the entire overhang length. Indeed, as shown in **FIG. 6**, the minimum separation distance **103** is maintained over the entire overhang length between the wire **125** and the outermost debonded edge of the first substrate **110** trailing behind the debonding front **107**. Supporting the overhang length can be achieved by applying a force having a force component opposite the direction of gravity. Supporting the overhang length to maintain the minimum separation distance **103** can be performed in a wide variety of ways. For example, one or more suction cups **135** may be used to support the debonded length **104**. In further embodiments, non-contact support devices (e.g., Bernoulli air chucks, etc.) may be used to support the debonded length **104**. Providing noncontact support can be beneficial to avoid damaging a pristine surface of the first substrate.

[0051] A top view of the composite substrate **100** is shown in **FIG. 7**. Prior to the step of moving the wire **125**, the first substrate **110** and the second substrate **120** may undergo one or more high temperature processes (e.g., anneal at about 150°C as well as other processes including temperatures within a range of about 150°C to about 700 °C, 250°C to about 600 °C or even greater than 700 °C) that increase a bond strength between the first substrate **110** and the second substrate **120**. In some embodiments, the bond strength can be as high as 800 mJ/m², 1000 mJ/m², or higher. In one embodiment, prior to the step of moving the wire **125**, functional components **145** (schematically illustrated in **FIG. 7**) can be applied to the second major surface **112** of the first substrate **110**. The functional components **145** can include thin film transistors (TFTs), photovoltaic (PV) devices, organic light emitting diodes (OLEDs), and liquid crystal display (LCD). In another embodiment, the method further includes the step of performing the step of moving the wire **125** until the first substrate **110** is entirely debonded from the second substrate **120** such that the first substrate **110** and the functional components **145** applied to the first substrate **110** can be separated from the second substrate **120**.

[0052] As shown in **FIG. 7**, the wire **125** is configured to conform to a shape of the debonding front **107** during the step of moving the wire **125** such that one or more edges **118** of the first substrate **110** (e.g., identified at locations **117**) are debonded from the second substrate **120** prior to a debonding of a corresponding interior portion (e.g., identified at location **119**) of the first substrate **110** from the second substrate **120**. For purposes of this application, the interior portion is considered to be a portion that includes a location **119** along an imaginary line **116** connecting the two locations **117** where the edges are debonded

at the debonding front **107**. As shown, the interior portion can also be considered to include the portion of the illustrated location **119** that is the midpoint of the imaginary line connecting the two locations **117**. Debonding of the two locations **117** prior to the corresponding interior portion can reduce stresses imposed on the edges of the first substrate that may be particularly vulnerable to edge failure due to edge imperfections. To achieve debonding at the locations **117** prior to the corresponding interior portion, the shape of the debonding front **107** can be concave with respect to the direction of propagation **130** of the debonding front **107**. Furthermore, due to the nature of the conformity of the wire **125** to a shape of the debonding front **107**, the debonding of the first substrate **110** from the second substrate **120** is maintained predominately as mode I (described above). Mode I has a lower debond or delamination energy than, for example, mode II. Therefore, the wire **125** and the debonding front **107** tend to move or conform to a shape or profile that maximizes mode I and minimizes mode II (e.g., minimizes adverse stresses in the first substrate **110**) during the debonding process.

[0053] Moreover, in the event of interaction of the wire **125** with any sharp transitions, flaws, or imperfections of the first substrate **110** (e.g., along one or more edges **118** of the first substrate **110**) or interaction with locations at the interface **115** of higher or stubborn bonding strength between the first substrate **110** and the second substrate **120**, the wire **125** is configured to at least one of yield and fail prior to a failure of the first substrate **110** to prevent any damage to the first substrate **110** and the second substrate **120**. The wire **125**, therefore, relieves or redistributes stress in the first substrate **110** that would otherwise occur if not for the pliable nature of the wire **125**. As noted, if the wire **125** at least one of yields and fails, the debonding process can be continued or repeated one or more times using a new wire **125** having at least one of an incrementally higher tensile strength and an incrementally larger diameter.

[0054] Many variations and modifications may be made to the above-described embodiments without departing substantially from the spirit and various principles described herein. All such modifications and variations are intended to be included herein within the scope of this disclosure and the following claims. Thus, it will be apparent to those skilled in the art that various modifications and variations can be made without departing from the spirit and scope of the following claims.

CLAIMS

1. A method of processing a first substrate bonded to a second substrate comprising the steps of:
 - initiating an opening at an interface between the first substrate and the second substrate;
 - inserting a wire into the opening; and
 - moving the wire along the interface to propagate a debonding front and debond the first substrate from the second substrate.
2. The method of claim 1, wherein the first substrate comprises a thickness less than or equal to about 300 μm .
3. The method of claim 1, wherein the wire comprises a diameter from about 50 μm to about 300 μm .
4. The method of claim 1, wherein the wire comprises a tensile strength from about 25 MPa to about 10 GPa.
5. The method of claim 1, wherein the wire is pliable.
6. The method of claim 5, wherein the wire comprises at least one of polytetrafluoroethylene (PTFE), nylon, and fluorocarbon.
7. The method of any one of claims 1-6, further comprising the step of:
 - maintaining at least a minimum separation distance between a debonded portion of the first substrate and a corresponding portion of the second substrate.
8. The method of claim 7, wherein the minimum separation distance is greater than or equal to a diameter of the wire.
9. The method of claim 7, wherein the minimum separation distance is maintained over an entire debonded length of the first substrate.

10. The method of any one of claims 1-6, wherein the wire comprises a first tensile strength less than a critical failure stress of the first substrate.

11. The method of claim 10, further comprising:

removing the wire;

inserting a new wire between the first substrate and the second substrate; and

moving the new wire along the interface to further propagate the debonding front and further debond the first substrate from the second substrate, wherein the new wire comprises a second tensile strength greater than the first tensile strength and less than the critical failure stress of the first substrate.

12. A method of processing a first substrate bonded to a second substrate comprising the steps of:

moving a wire along an interface between the first substrate and the second substrate to propagate a debonding front and debond the first substrate from the second substrate, wherein the first substrate comprises a thickness less than or equal to about 300 μm , and wherein the wire comprises a tensile strength less than a critical failure stress of the first substrate.

13. The method of claim 1 or claim 12, further comprising maintaining a debond angle substantially constant during the step of moving the wire.

14. The method of claim 1 or claim 12, wherein prior to the step of moving the wire, increasing a bond strength between the first substrate and the second substrate by raising the temperature of the first substrate and the second substrate to a temperature of at least about 150°C.

15. The method of claim 1 or claim 12, wherein prior to the step of moving the wire, applying functional components to a major surface of the first substrate facing away from the second substrate bonded to the first substrate.

16. The method of claim 1 or claim 12, wherein the step of moving the wire entirely debonds the first substrate from the second substrate.

17. The method of claim 1 or claim 12, wherein the wire is configured to conform to a shape of the debonding front during the step of moving the wire such that one or more edges of the first substrate are debonded from the second substrate prior to a debonding of a corresponding interior portion of the first substrate from the second substrate.

18. The method of claim 17, wherein the shape of the debonding front is concave with respect to a direction of propagation of the debonding front.

19. The method of claim 17, wherein the wire is configured to at least one of yield and fail prior to a failure of the first substrate.

20. The method of claim 17, wherein a bond strength at the debonding front is defined based, at least in part, on at least one of a wafer bonding between the first substrate and the second substrate and a bonding agent between the first substrate and the second substrate.

1 / 3

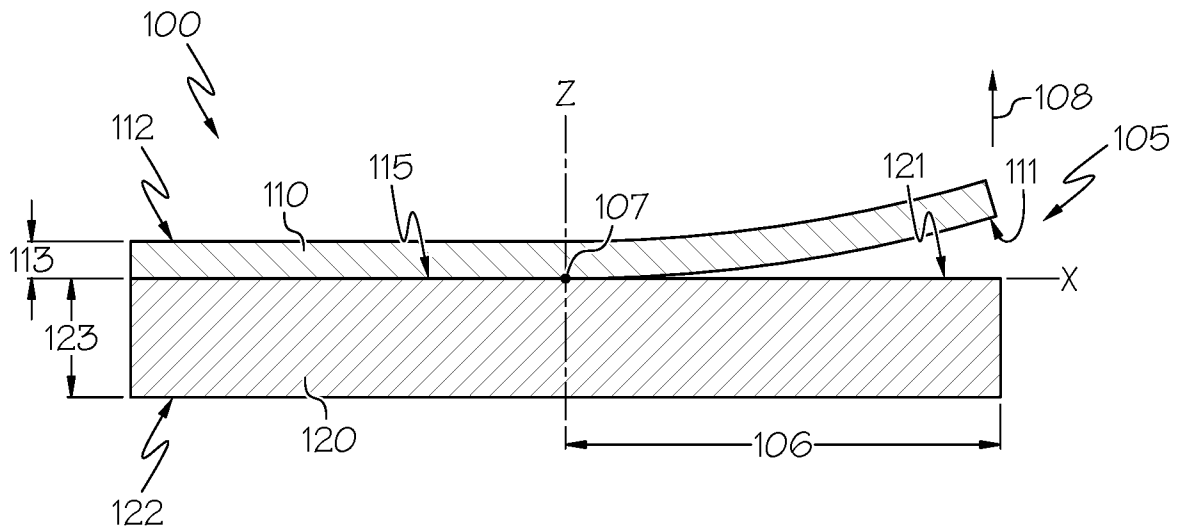


FIG. 1

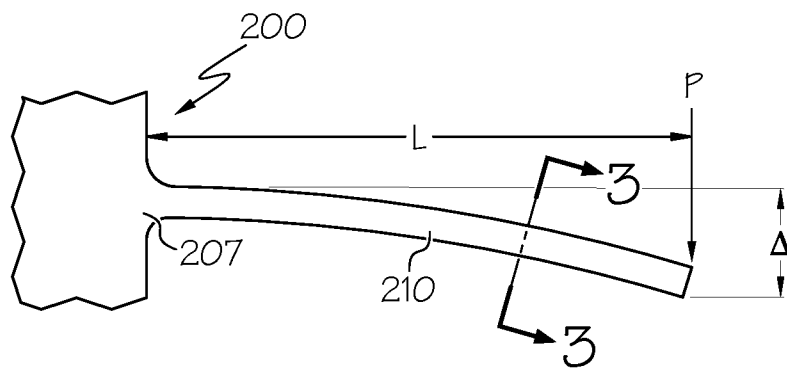


FIG. 2

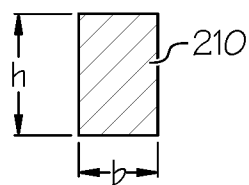


FIG. 3

2 / 3

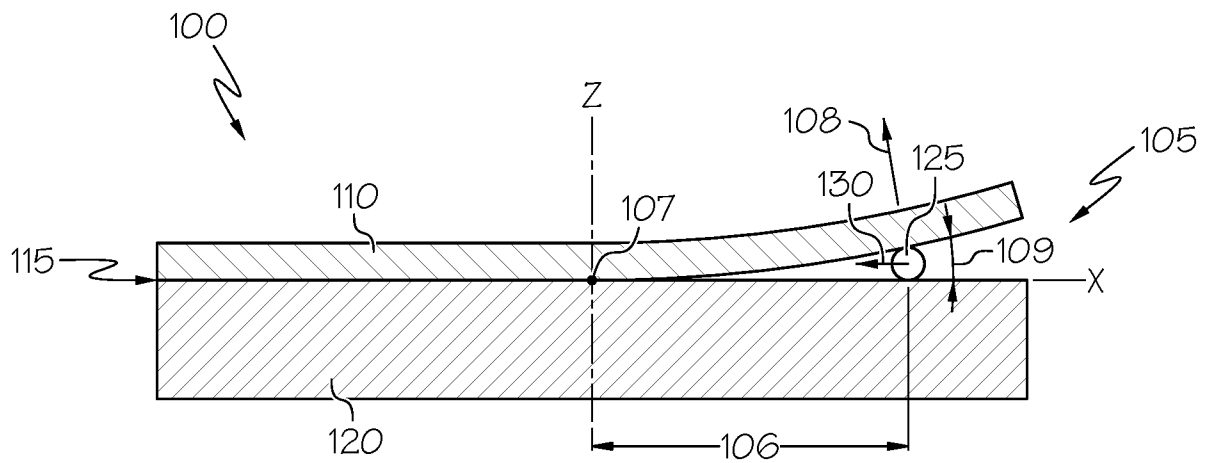


FIG. 4

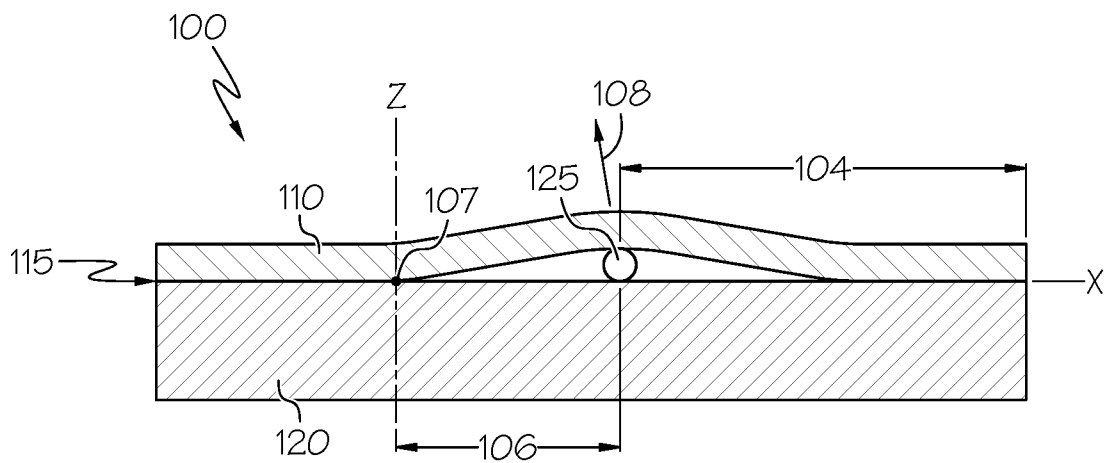


FIG. 5

3 / 3

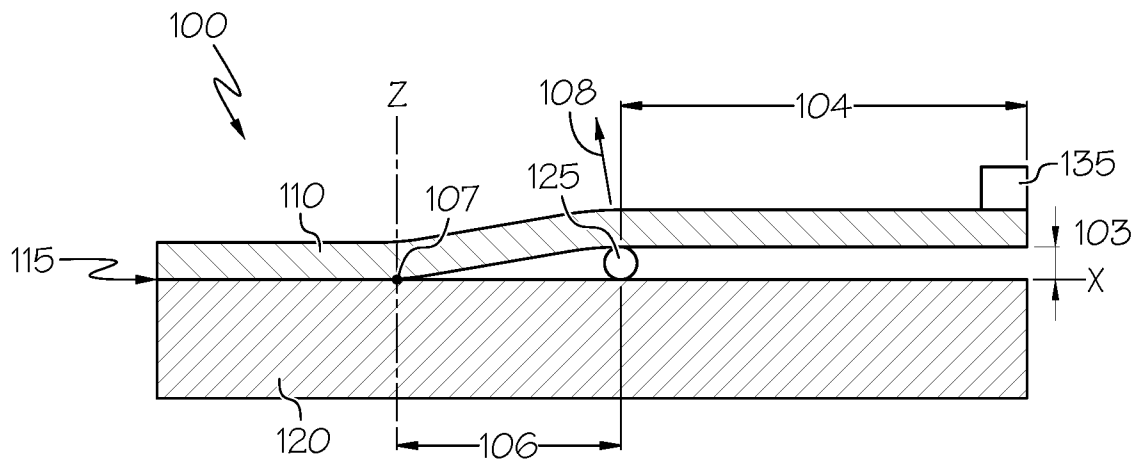


FIG. 6

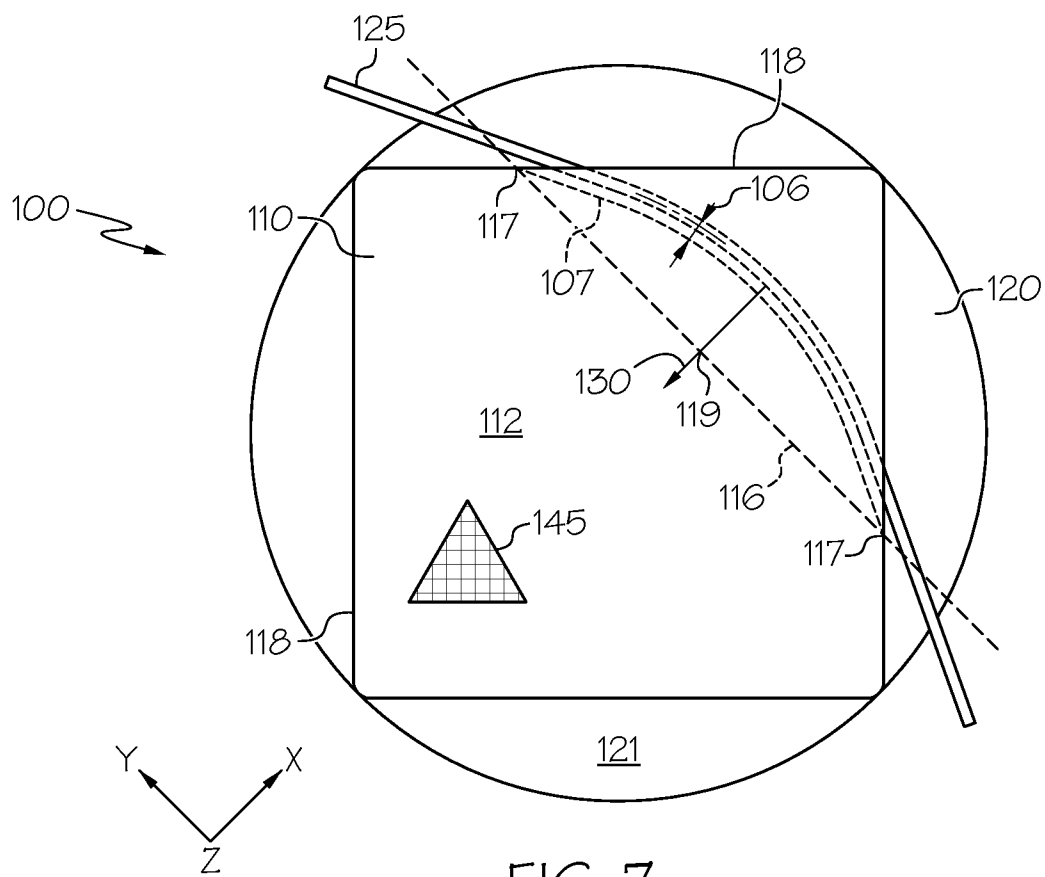


FIG. 7

INTERNATIONAL SEARCH REPORT

International application No.
PCT/US2016/059014**A. CLASSIFICATION OF SUBJECT MATTER****H05K 3/40(2006.01)i, H05K 1/03(2006.01)i**

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHEDMinimum documentation searched (classification system followed by classification symbols)
H05K 3/40; B32B 43/00; H05K 13/04; B32B 37/06; B32B 38/10; B32B 37/08; H05K 1/03Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched
Korean utility models and applications for utility models
Japanese utility models and applications for utility modelsElectronic data base consulted during the international search (name of data base and, where practicable, search terms used)
eKOMPASS(KIPO internal) & Keywords: debonding, substrate, wire, debonding front, tensile strength, critical failure stress**C. DOCUMENTS CONSIDERED TO BE RELEVANT**

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 2014-0196854 A1 (E INK HOLDINGS INC.) 17 July 2014 See paragraphs [0025]–[0029] and figures 1–2.	1–20
A	JP 2001-210998 A (DENSO CORP.) 03 August 2001 See paragraphs [0016]–[0022] and figures 1–2.	1–20
A	US 2012-0138237 A1 (TAKAAKI HIRANO) 07 June 2012 See paragraphs [0072]–[0080] and figures 9–12.	1–20
A	US 2008-0308231 A1 (JAE-SEOB LEE et al.) 18 December 2008 See paragraphs [0055]–[0057] and figures 3A–3B.	1–20
A	US 2015-0290921 A1 (SAMSUNG DISPLAY CO., LTD.) 15 October 2015 See paragraphs [0030]–[0063] and figures 1–2E.	1–20



Further documents are listed in the continuation of Box C.



See patent family annex.

* Special categories of cited documents:

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"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search

20 January 2017 (20.01.2017)

Date of mailing of the international search report

20 January 2017 (20.01.2017)

Name and mailing address of the ISA/KR

International Application Division

Korean Intellectual Property Office

189 Cheongsa-ro, Seo-gu, Daejeon, 35208, Republic of Korea

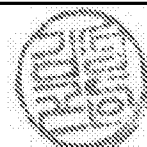


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INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

PCT/US2016/059014

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